

Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
Common Ratings ($T_A=25^{\circ}\text{C}$ Unless Otherwise Noted)			
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	
T_J	Maximum Junction Temperature	150	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	
I_S	Diode Continuous Forward Current	$T_C=25^{\circ}\text{C}$	A
I_D	Continuous Drain Current	$T_C=25^{\circ}\text{C}$	40
		$T_C=100^{\circ}\text{C}$	25
I_{DM}^{a}	Pulsed Drain Current	$T_C=25^{\circ}\text{C}$	160
P_D	Maximum Power Dissipation	$T_C=25^{\circ}\text{C}$	83
		$T_C=100^{\circ}\text{C}$	33
$R_{\theta\text{JC}}$	Thermal Resistance-Junction to Case	1.5	$^{\circ}\text{C/W}$
I_D	Continuous Drain Current	$T_A=25^{\circ}\text{C}$	6.7
		$T_A=70^{\circ}\text{C}$	5.3
P_D	Maximum Power Dissipation	$T_A=25^{\circ}\text{C}$	2.5
		$T_A=70^{\circ}\text{C}$	1.6
$R_{\theta\text{JA}}$	Thermal Resistance-Junction to Ambient	50	$^{\circ}\text{C/W}$
I_{AS}^{b}	Avalanche Current, Single pulse ($L=0.5\text{mH}$)	18	A
E_{AS}^{b}	Avalanche Energy, Single pulse ($L=0.5\text{mH}$)	81	mJ

Note a: Pulse width is limited by max. junction temperature.

b: UIS tested and pulse width are limited by maximum junction temperature 150°C (initial temperature $T_J=25^{\circ}\text{C}$).

Electrical Characteristics ($T_A = 25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV_{DS}	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}$, $I_{\text{DS}}=250\mu\text{A}$	100	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{\text{DS}}=80\text{V}$, $V_{\text{GS}}=0\text{V}$	-	-	1	μA
		$T_J=85^{\circ}\text{C}$	-	-	30	
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{\text{DS}}=V_{\text{GS}}$, $I_{\text{DS}}=250\mu\text{A}$	1	2	3	V
I_{GSS}	Gate Leakage Current	$V_{\text{GS}}=\pm 20\text{V}$, $V_{\text{DS}}=0\text{V}$	-	-	± 100	nA
$R_{\text{DS(ON)}}^{\text{c}}$	Drain-Source On-state Resistance	$V_{\text{GS}}=10\text{V}$, $I_{\text{DS}}=20\text{A}$	-	22	28	$\text{m}\Omega$
		$V_{\text{GS}}=4.5\text{V}$, $I_{\text{DS}}=15\text{A}$	-	24	32	$\text{m}\Omega$

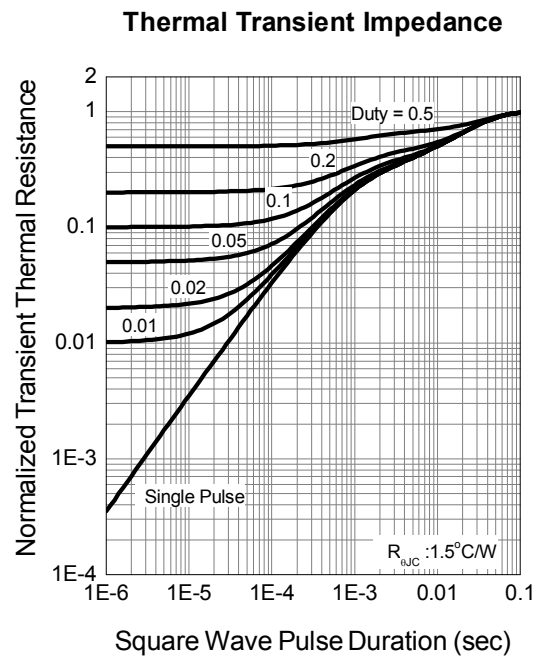
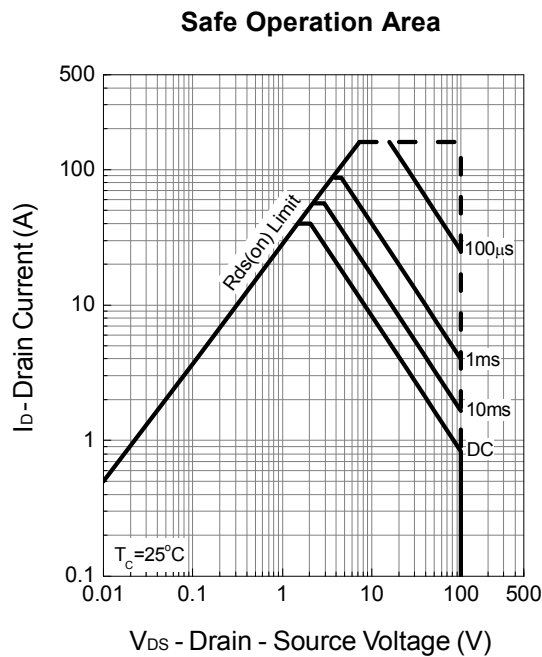
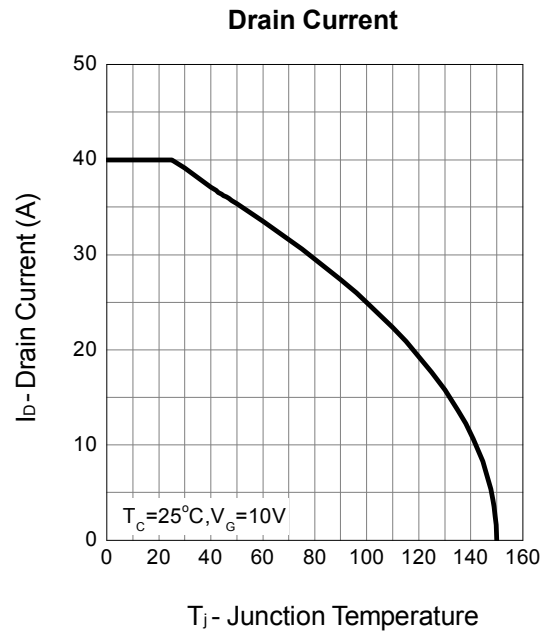
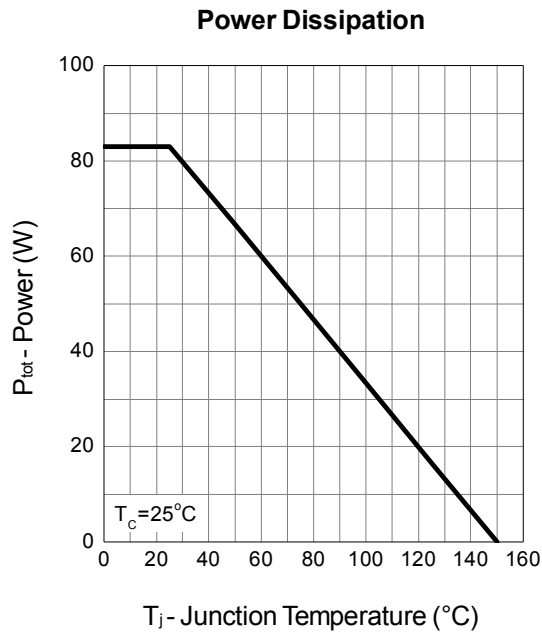
Electrical Characteristics (Cont.) ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Diode Characteristics						
V _{SD} ^c	Diode Forward Voltage	I _{SD} =20A, V _{GS} =0V	-	0.8	1.3	V
t _{rr}	Reverse Recovery Time	I _{SD} =20A, dI _{SD} /dt=100A/μs	-	40	-	ns
Q _{rr}	Reverse Recovery Charge		-	83	-	nC
Dynamic Characteristics ^d						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz	-	1.0	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =30V, Frequency=1.0MHz	-	2450	3180	pF
C _{oss}	Output Capacitance		-	150	-	
C _{rss}	Reverse Transfer Capacitance		-	85	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =30V, R _L =30Ω, I _{DS} =1A, V _{GEN} =10V, R _G =6Ω	-	18	33	ns
t _r	Turn-on Rise Time		-	9	17	
t _{d(OFF)}	Turn-off Delay Time		-	56	101	
t _f	Turn-off Fall Time		-	14	26	
Gate Charge Characteristics ^d						
Q _g	Total Gate Charge	V _{DS} =30V, V _{GS} =4.5V, I _{DS} =20A	-	24	-	nC
Q _g	Total Gate Charge	V _{DS} =30V, V _{GS} =10V, I _{DS} =20A	-	50	65	
Q _{gs}	Gate-Source Charge		-	8	-	
Q _{gd}	Gate-Drain Charge		-	10	-	

Note c: Pulse test; pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.

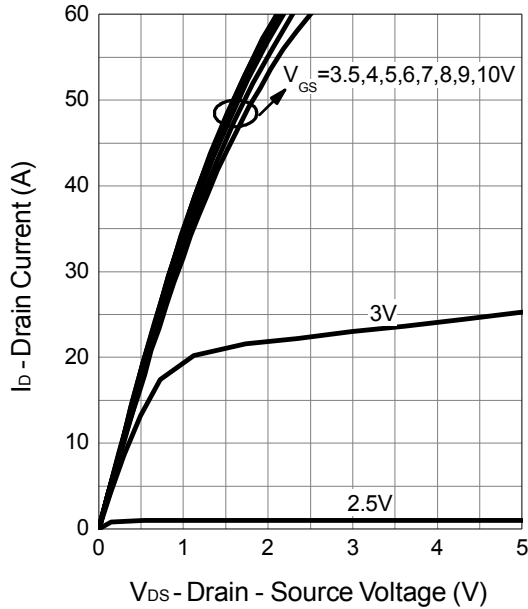
d: Guaranteed by design, not subject to production testing.

Typical Operating Characteristics

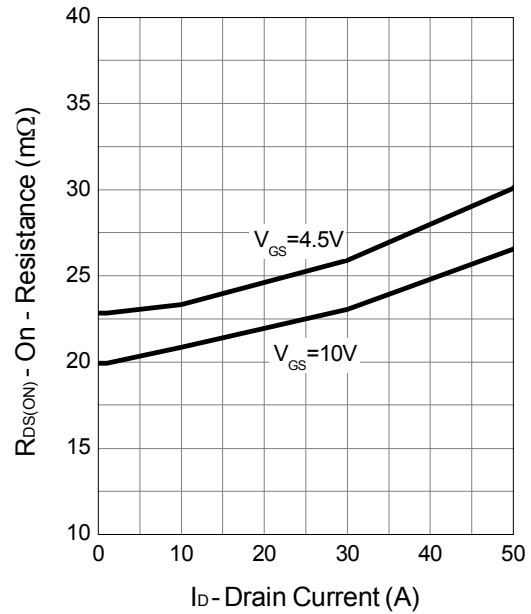


Typical Operating Characteristics (Cont.)

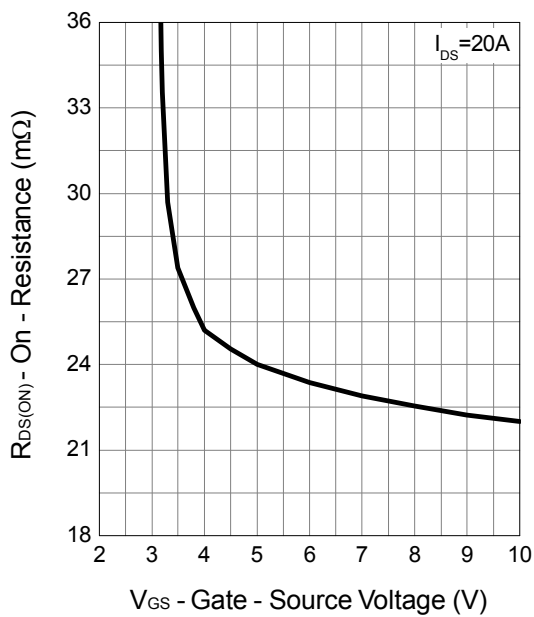
Output Characteristics



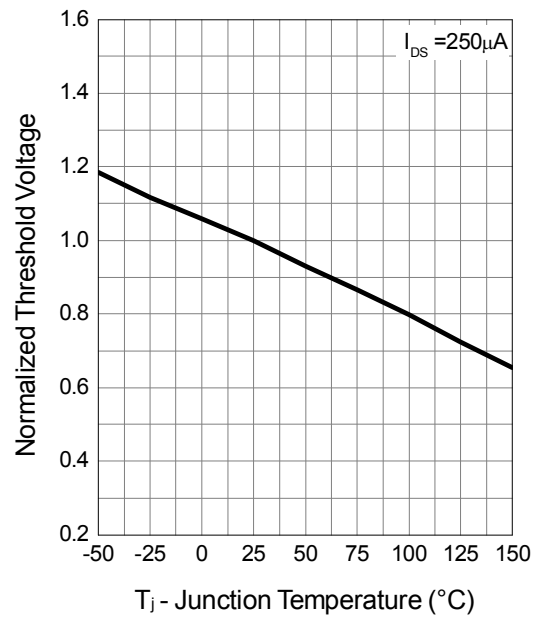
Drain-Source On Resistance



Gate-Source On Resistance

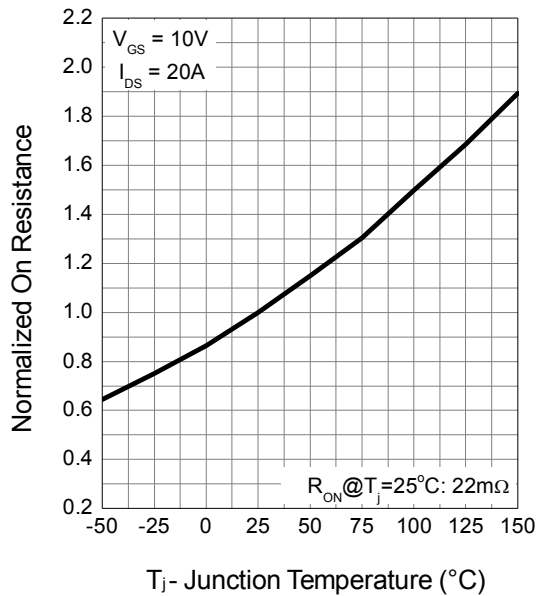


Gate Threshold Voltage

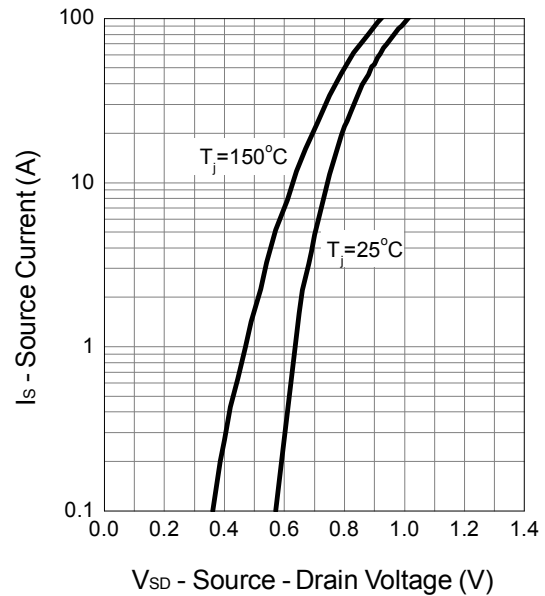


Typical Operating Characteristics (Cont.)

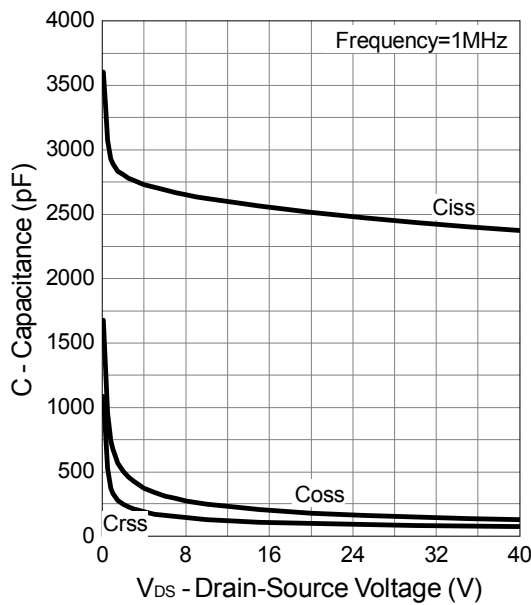
Drain-Source On Resistance



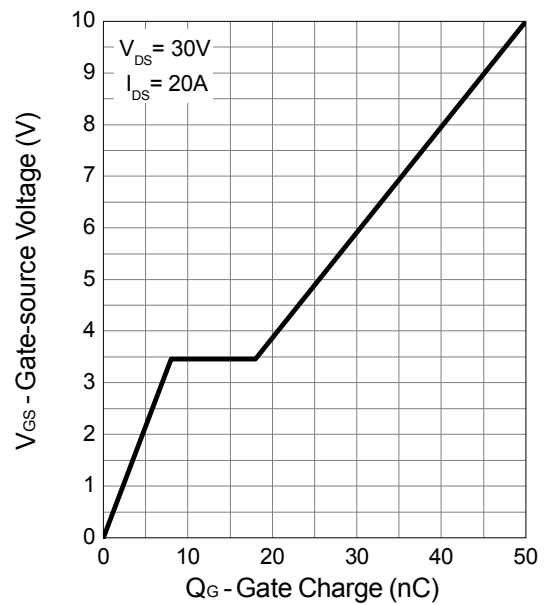
Source-Drain Diode Forward



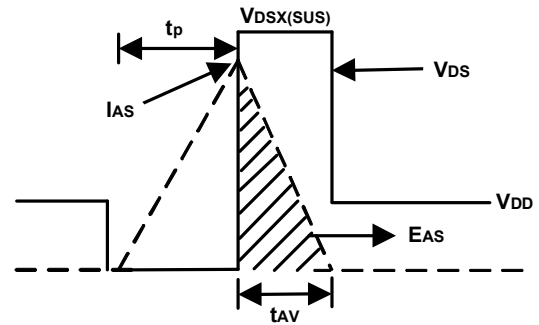
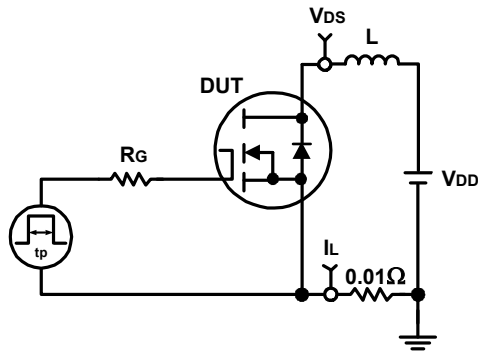
Capacitance



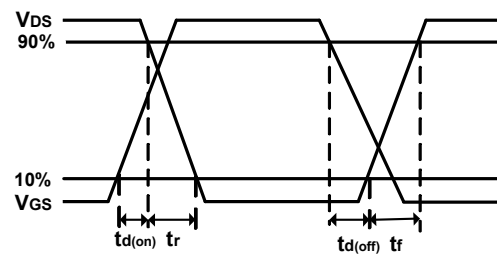
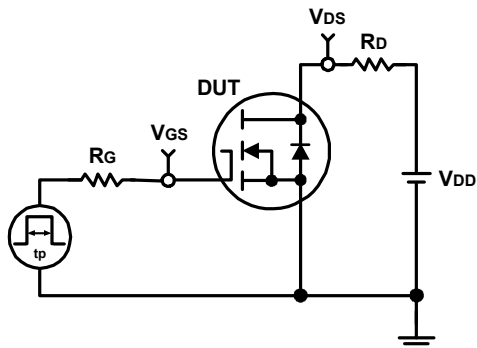
Gate Charge



Avalanche Test Circuit and Waveforms

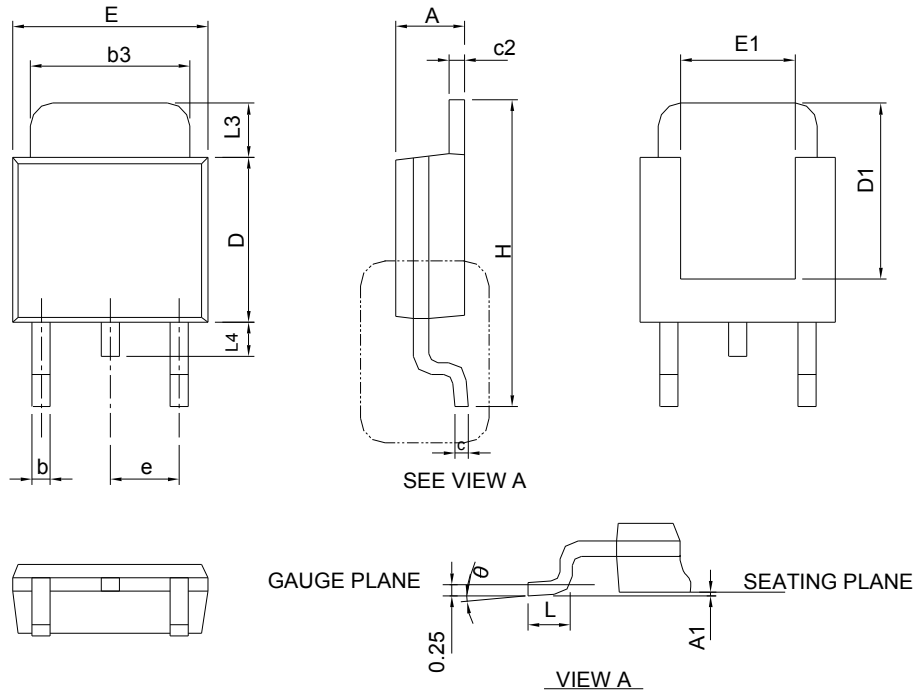


Switching Time Test Circuit and Waveforms



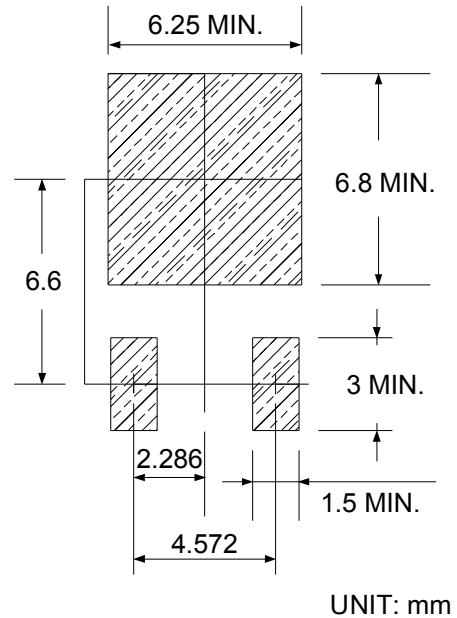
Package Information

TO-252-3



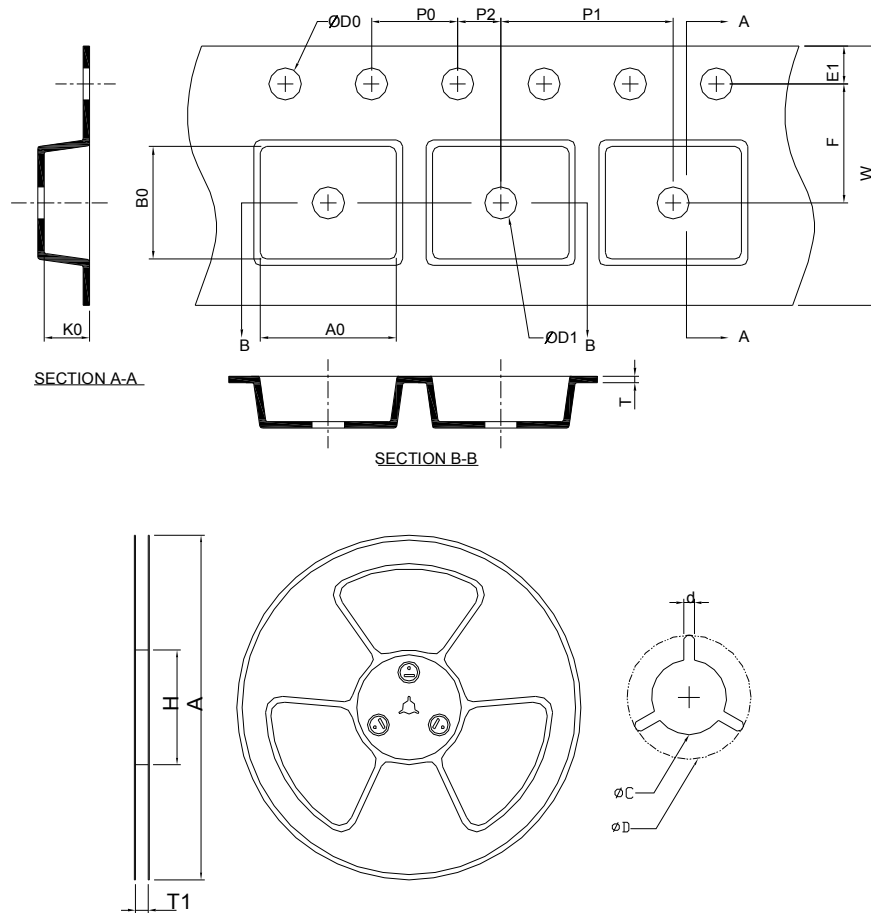
DIMENSIONS	TO-252-3			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.18	2.39	0.086	0.094
A1	-	0.13	-	0.005
b	0.50	0.89	0.020	0.035
b3	4.95	5.46	0.195	0.215
c	0.46	0.61	0.018	0.024
c2	0.46	0.89	0.018	0.035
D	5.33	6.22	0.210	0.245
D1	4.57	6.00	0.180	0.236
E	6.35	6.73	0.250	0.265
E1	3.81	6.00	0.150	0.236
e	2.29 BSC		0.090 BSC	
H	9.40	10.41	0.370	0.410
L	0.90	1.78	0.035	0.070
L3	0.89	2.03	0.035	0.080
L4	-	1.02	-	0.040
θ	0°	8°	0°	8°

RECOMMENDED LAND PATTERN



Note : Follow JEDEC TO-252 .

Carrier Tape & Reel Dimensions

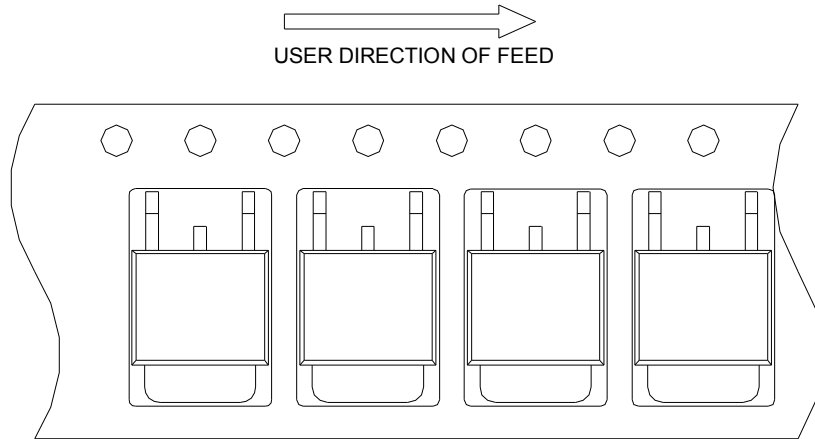


Application	A	H	T1	C	d	D	W	E1	F
TO-252-3	330.0 ± 2.00	50 MIN.	$16.4 + 2.00 - 0.00$	$13.0 + 0.50 - 0.20$	1.5 MIN.	20.2 MIN.	16.0 ± 0.30	1.75 ± 0.10	7.50 ± 0.05
	P0	P1	P2	D0	D1	T	A0	B0	K0
	4.0 ± 0.10	8.0 ± 0.10	2.0 ± 0.05	$1.5 + 0.10 - 0.00$	1.5 MIN.	$0.6 + 0.00 - 0.40$	6.80 ± 0.20	10.40 ± 0.20	2.50 ± 0.20

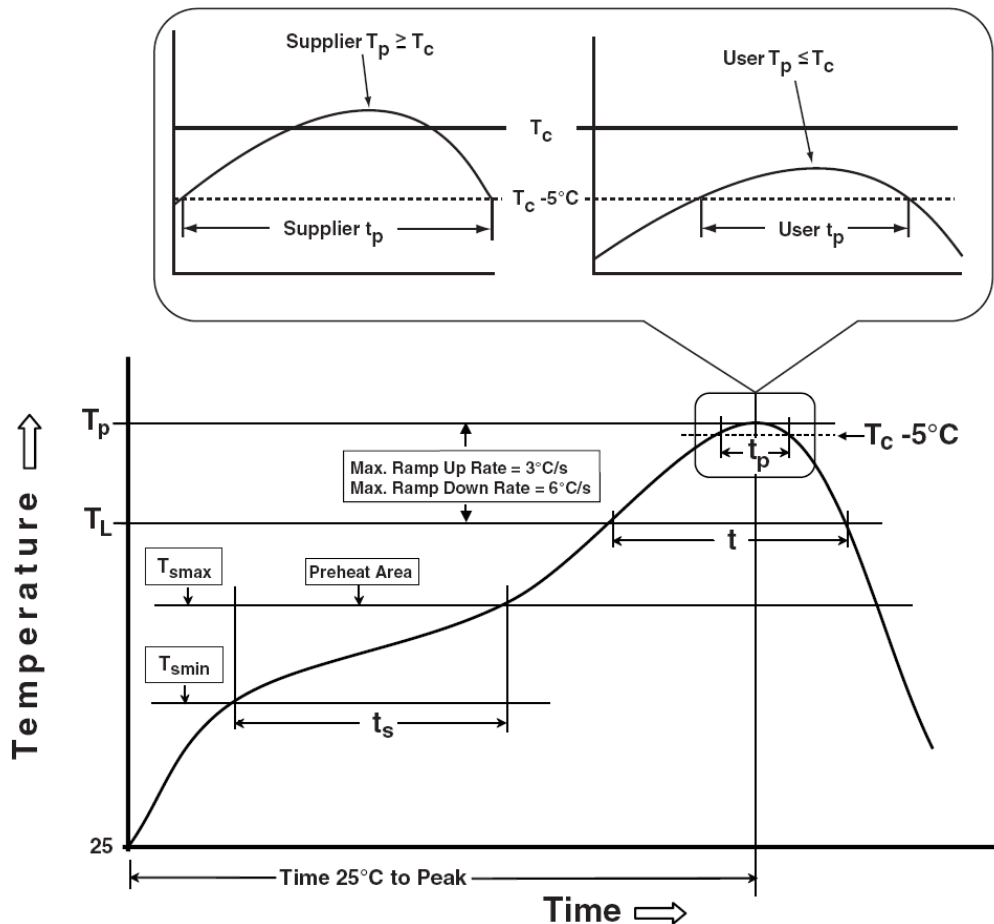
(mm)

Taping Direction Information

TO-252-3



Classification Profile



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak Temperature min (T_{smin}) Temperature max (T_{smax}) Time (T_{smin} to T_{smax}) (t_s)	100 °C 150 °C 60-120 seconds	150 °C 200 °C 60-120 seconds
Average ramp-up rate (T_{smax} to T_p)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L) Time at liquidous (t_L)	183 °C 60-150 seconds	217 °C 60-150 seconds
Peak package body Temperature (T_p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_p)** within 5°C of the specified classification temperature (T_c)	20** seconds	30** seconds
Average ramp-down rate (T_p to T_{smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature (T_p) is defined as a supplier minimum and a user maximum. ** Tolerance for time at peak profile temperature (t_p) is defined as a supplier minimum and a user maximum.		

Table 1. SnPb Eutectic Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

Reliability Test Program

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
HTRB	JESD-22, A108	1000 Hrs, 80% of VDS max @ T_{jmax}
HTGB	JESD-22, A108	1000 Hrs, 100% of VGS max @ T_{jmax}
PCT	JESD-22, A102	168 Hrs, 100%RH, 2atm, 121°C
TCT	JESD-22, A104	500 Cycles, -65°C~150°C

Customer Service

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